General Description

The WSF35N20 is the highest performance SGT N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSF35N20 meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
200V	60mΩ	35A

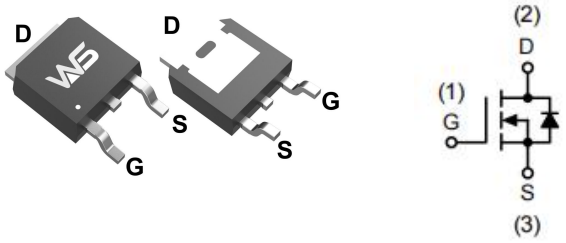
Applications

- Power Management for Industrial DC/DC Converters

Features

- 100% UIS + R_g Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

TO-252-2L Pin Configuration



Absolute Maximum Ratings (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		200	V
V_{GS}	Gate-Source Voltage		±20	
I_D [7]	Continuous Drain Current	T_C=25°C	35	A
		T_C=100°C	20	
I_{DM} [3]	Pulse Drain Current		140	
P_D [2]	Power Dissipation	T_C=25°C	150	W
		T_C=100°C	62	
I_{AS} [3]	Single pulse Avalanche Current		20	A
E_{AS} [3]	Single pulse Avalanche Energy	L=0.5mH	360	mJ
T_{STG}	Storage Temperature Range		-55 to 150	°C
T_J	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ [1,4]	Thermal Resistance-Junction to Ambient	t≤10s	31	°C/W
		Steady State	62.5	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		0.83	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	60	65	mΩ
		T_J=125°C	---	77	80	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250μA	2.0	3.0	4.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=200V , V_{GS}=0V	---	---	1.0	μA
		T_J=55°C	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V , V_{GS}=±20V	---	---	±100	nA
g_{fs}	Forward Transconductance	V_{DS}=5V , I_D=20A	---	15	---	S
R_G	Gate Resistance	f=1.0MHz	1.0	2.0	3.1	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=160V , V_{GS}=10V , I_D=20A	---	50	---	nC
Q_g	Total Gate Charge (4.5V)		---	34	---	
Q_{gs}	Gate-Source Charge		---	16.5	---	
Q_{gd}	Gate-Drain Charge		---	23	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V , V_{GS}=10V , R_L=1Ω , R_{GEN}=3Ω	---	12.5	---	ns
T_r	Rise Time		---	25	---	
$T_{d(off)}$	Turn-Off Delay Time		---	32	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1.0MHz	---	2762	---	pF
C_{oss}	Output Capacitance		---	361	---	
C_{rss}	Reverse Transfer Capacitance		---	53	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S [7]	Continuous Source Current		---	---	35	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A	---	---	1.4	V
t_{rr}	Reverse Recovery Time	I_F=20A , di/dt=500A/μs	---	233	---	ns
Q_{rr}	Reverse Recovery Charge		---	2.1	---	nC

Note:

1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
2. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
4. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
5. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
6. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.
7. The maximum current rating is package limited.
8. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
9. The maximum current rating is silicon limited

Typical Characteristics

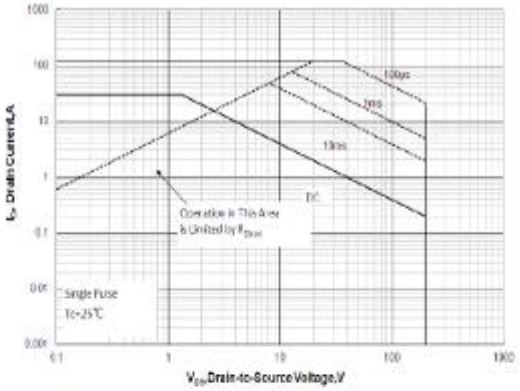


Figure 1 Maximum Forward Bias Safe Operating Area

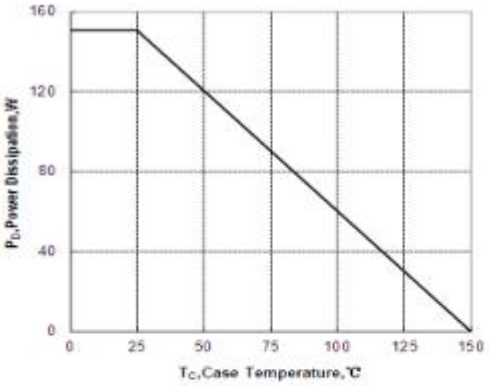


Figure 2 Maximum Power dissipation vs Case Temperature

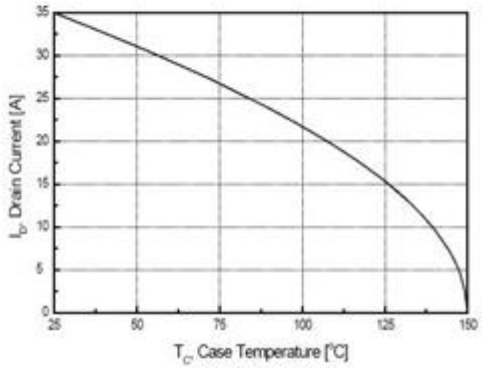


Figure 3 Maximum Continuous Drain Current vs Case Temperature

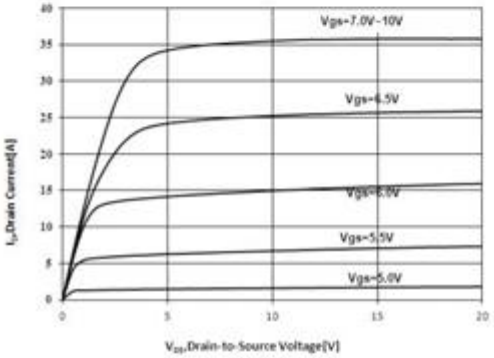


Figure 4 Typical Output Characteristics

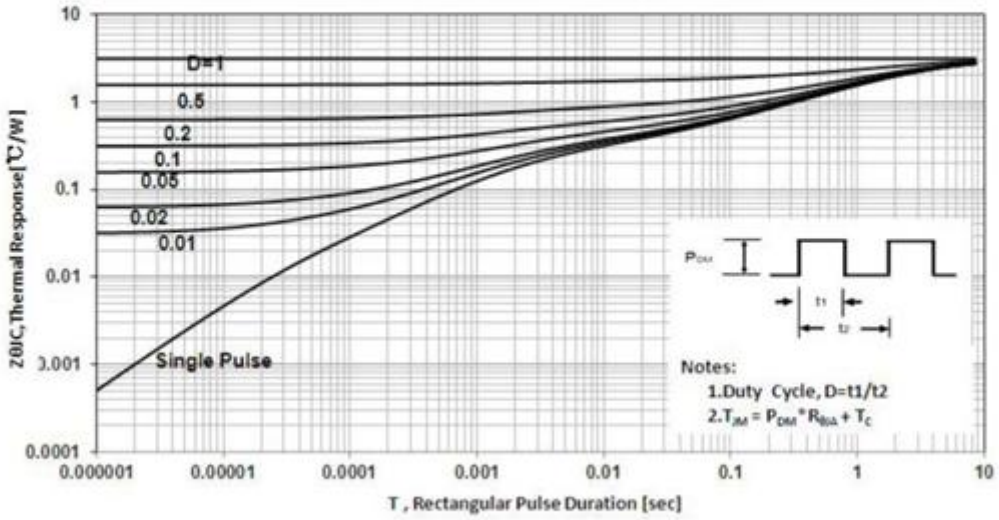


Figure 5 Maximum Effective Thermal Impedance , Junction to Case

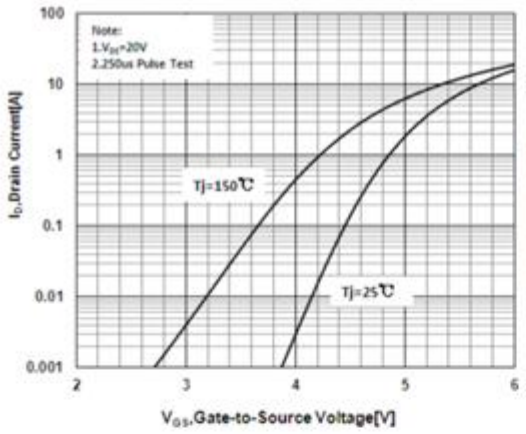


Figure 6 Typical Transfer Characteristics

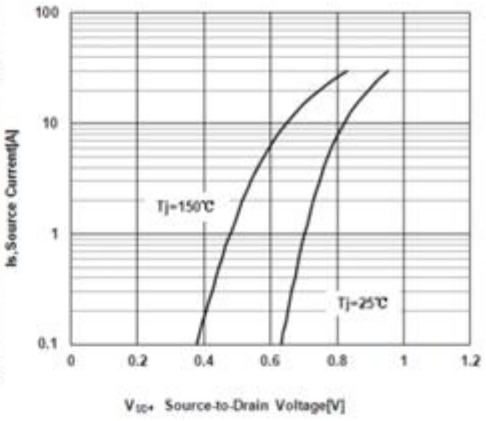


Figure 7 Typical Body Diode Transfer Characteristics

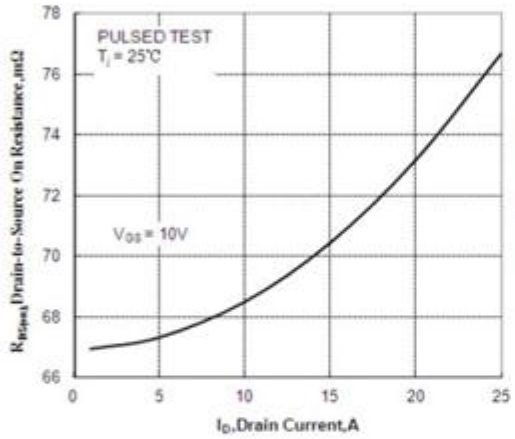


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

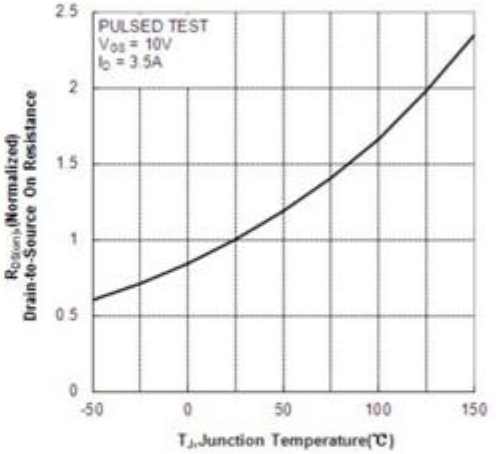
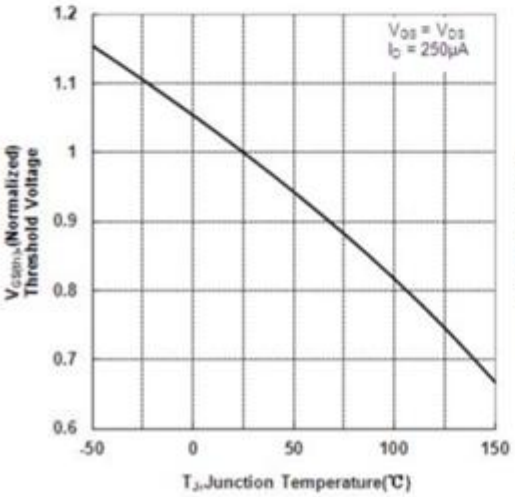
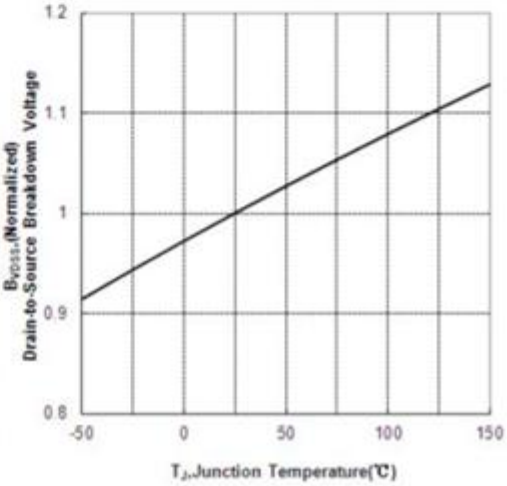
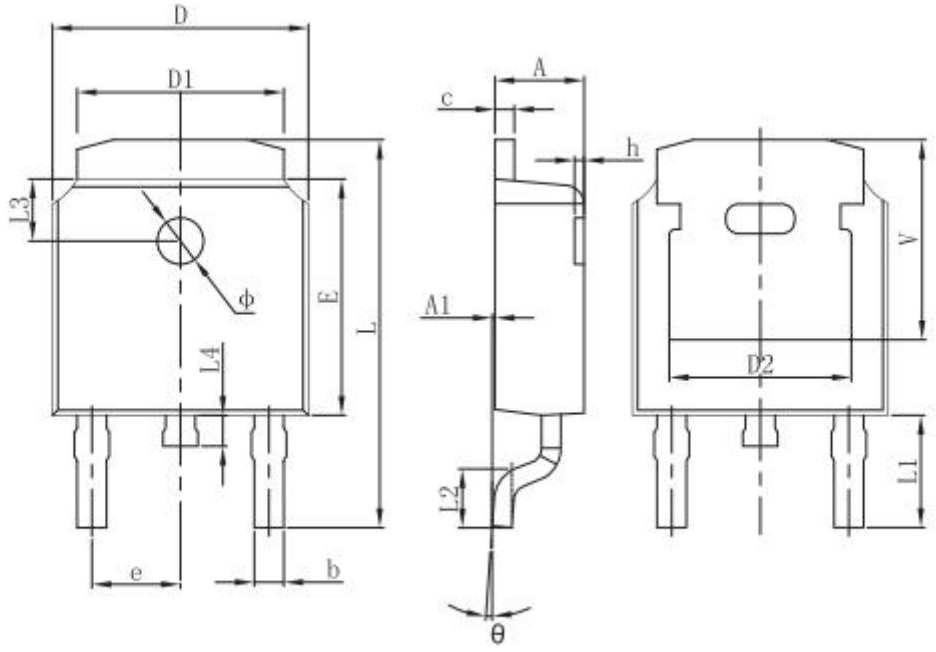


Figure 9 Typical Drian to Source on Resistance vs Junction Temperature





Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

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